

Time table (tentative)

November 16

8:00	
8:10	
8:20	
8:30	
8:40	
8:50	
9:00	Registration
9:10	
9:20	
9:30	
9:40	Opening Remark (M. Matsui), Award Ceremony (H. Akatsuka)
9:50	
10:00	
10:10	
10:20	<Nishizawa Award Lecture> Prof. David Barry Graves, Prof. Toshiaki Makabe
10:30	
10:40	
10:50	Keynote <Invited>
11:00	Dan Mocuta (imec)
11:10	
11:20	Break 20min
11:30	
11:40	A-1
11:50	
12:00	A-2
12:10	
12:20	A-3
12:30	
12:40	
12:50	
13:00	
13:10	Lunch 12:40-14:00 (80min)
13:20	
13:30	
13:40	
13:50	
14:00	
14:10	B-1 <Invited>
14:20	Simon Elliott (Univ. College Cork)
14:30	
14:40	
14:50	B-2 <Invited>
15:00	Dennis Hausmann (Lam Research Corp.)
15:10	
15:20	B-3
15:30	
15:40	
15:50	Break 20min
16:00	
16:10	C-1
16:20	
16:30	C-2
16:40	
16:50	Break 10min
17:00	D-1
17:10	
17:20	D-2
17:30	
17:40	D-3
17:50	
18:00	D-4
18:10	
18:20	
18:30	
18:40	
18:50	
19:00	
19:10	
19:20	Banquet
19:30	
19:40	
19:50	
20:00	
20:10	
20:20	
20:30	

Session A
Etching
Technologies

Session B
Surface
reactions for
atomic layer
controlled
processes
(ALD/CVD)

Session C
Plasma
Diagnostics &
Monitoring

Session D
New Dry
Process and
Equipment

November 17

8:00	
8:10	
8:20	
8:30	
8:40	
8:50	
9:00	Registration
9:10	
9:20	
9:30	
9:40	E-1
9:50	
10:00	E-2
10:10	
10:20	E-3
10:30	
10:40	E-4
10:50	
11:00	E-5
11:10	
11:20	
11:30	
11:40	
11:50	
12:00	Poster 100min
12:10	
12:20	
12:30	
12:40	
12:50	
13:00	
13:10	Lunch 12:50-13:50 (60min)
13:20	
13:30	
13:40	
13:50	
14:00	F-1 <Invited>
14:10	Yoon-Jae Kim (Samsung Electronics Co., Ltd.)
14:20	
14:30	
14:40	F-2 <Invited>
14:50	Aaron Wilson (Micron Technology, Inc.)
15:00	
15:10	
15:20	Break 20min
15:30	
15:40	F-3 <Invited>
15:50	Mark J. Kushner (Univ. of Michigan)
16:00	
16:10	F-4
16:20	
16:30	F-5
16:40	
16:50	Break 10min
17:00	
17:10	G-1
17:20	
17:30	G-2
17:40	
17:50	G-3
18:00	Closing Remark (M. Fukasawa)
18:10	
18:20	
18:30	
18:40	
18:50	
19:00	
19:10	
19:20	
19:30	
19:40	
19:50	
20:00	
20:10	
20:20	
20:30	

Session E
Surface
reactions for
atomic layer
controlled
processes
(ALE)

Session F
Etching
technologies
for latest
devices
having high-
aspect-ratio
of 50 or
more (HAR)

Session G
Damage